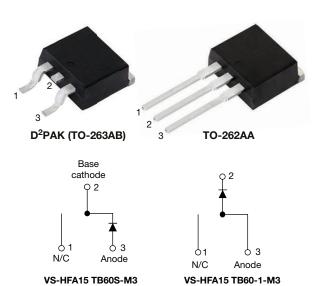


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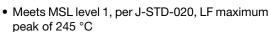
HEXFRED®, Ultrafast Soft Recovery Diode, 15 A



PRIMARY CHARACTERISTICS					
I _{F(AV)}	15 A				
V_{R}	600 V				
V _F at I _F	1.2 V				
t _{rr} (typ.)	23 ns				
T_J max.	150 °C				
Package	D ² PAK (TO-263AB), TO-262AA				
Circuit configuration	Single				

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}





- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- · Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA15TB60S, VS-HFA15TB60-1 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the VS-HFA15TB60S, VS-HFA15TB60-1 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and HEXFRED heatsink sizes. The VS-HFA15TB60S. VS-HFA15TB60-1 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V _R		600	V	
Maximum continuous forward current	I _F	T _C = 100 °C	15		
Single pulse forward current	I _{FSM}		150	Α	
Maximum repetitive forward current	I _{FRM}		60		
Maximum navay dissination	P _D	T _C = 25 °C	74	W	
Maximum power dissipation		T _C = 100 °C	29]	
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C	

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VS-HFA15TB60S-M3, VS-HFA15TB60-1-M3

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	I _R = 100 μA		600	-	-	
		I _F = 15 A		-	1.3	1.7	V
Maximum forward voltage	V_{FM}	I _F = 30 A	See fig. 1	-	1.5	2.0	
		I _F = 15 A, T _J = 125 °C		-	1.2	1.6	
Maximum reverse		$V_R = V_R$ rated	Coo fig. 0	-	1.0	10	
leakage current	I _{RM}	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See fig. 2	-	400	1000	μA
Junction capacitance	C _T	V _R = 200 V	See fig. 3	-	25	50	pF
Series inductance	L _S	Measured lead to lead 5 mm from page 1	ackage body	-	8.0	-	nΗ

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST COM	TEST CONDITIONS			MAX.	UNITS	
Reverse recovery time See fig. 5	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	√μs, V _R = 30 V	-	23	-	ns	
	t _{rr1}	T _J = 25 °C	I _F = 15 A	-	50	60		
	t _{rr2}	T _J = 125 °C		-	105	120		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.5	6.0	- A	
See fig. 6	I _{RRM2}	T _J = 125 °C		-	6.5	10		
Reverse recovery charge	Q _{rr1}	$T_J = 25 ^{\circ}C$	dl _F /dt = 200 A/μs V _R = 200 V	-	84	180		
See fig. 7	Q _{rr2} T _J = 125 °C	-	241	600	110			
Peak rate of fall of recovery	dI _{(rec)M} /dt1	T _J = 25 °C		-	188	-		
current during t _b See fig. 8	dI _{(rec)M} /dt2	T _J = 125 °C		-	160	-	A/µs	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.7		
Thermal resistance, junction-to-ambient	R _{thJA}	Typical socket mount	-	-	80	K/W	
Thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	i		
Weight			-	2.0	-	g	
vveignt			-	0.07	-	oz.	
Marking device		Case style D ² PAK (TO-263AB)	HFA15TB60S				
ivial killig device		Case style TO-262AA		HFA15	TB60-1		

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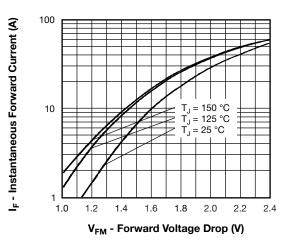


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

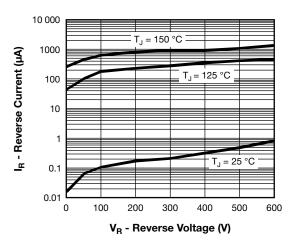


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

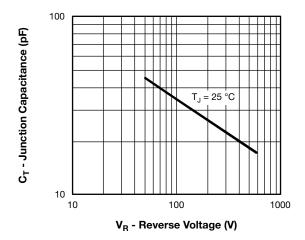


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

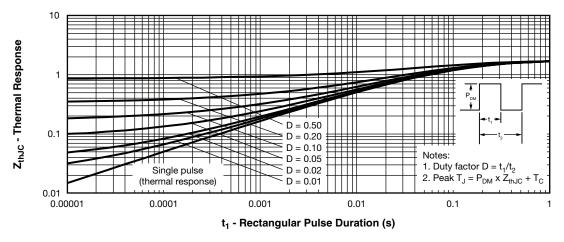


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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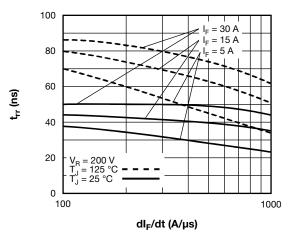


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

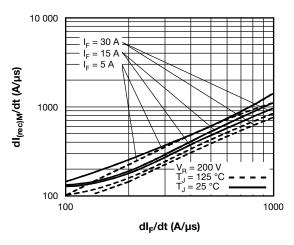


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

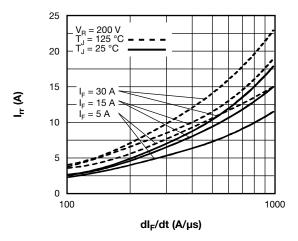


Fig. 6 - Typical Recovery Current vs. dI_F/dt

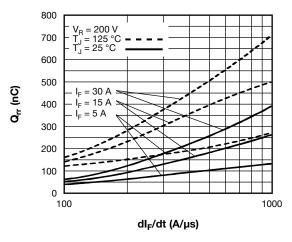
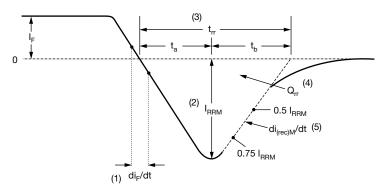


Fig. 7 - Typical Stored Charge vs. dI_F/dt

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VS-HFA15TB60S-M3, VS-HFA15TB60-1-M3

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- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm l_F$ to point where a line passing through 0.75 $\rm l_{RRM}$ and 0.50 $\rm l_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

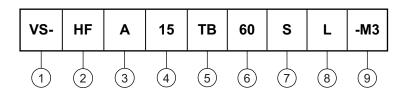


VS-HFA15TB60S-M3, VS-HFA15TB60-1-M3

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - HEXFRED® family

3 - Electron irradiated

4 - Current rating (15 = 15 A)

5 - Package:

TB = TO-220

6 - Voltage rating (60 = 600 V)

 $\overline{7}$ - • S = D²PAK (TO-263AB)

- • -1 = TO-262AA

• None = tube (50 pieces)

• L = tape and reel (left oriented, for D²PAK (TO-263AB) package)

• R = tape and reel (right oriented, for D²PAK (TO-263AB) package)

9 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	PREFERRED P/N BASE QUANTITY PACKAGING DESCRIPTION						
VS-HFA15TB60S-M3	50	Antistatic plastic tube					
VS-HFA15TB60SL-M3	800	13" diameter reel					
VS-HFA15TB60SR-M3	800	13" diameter reel					
VS-HFA15TB60-1-M3	50	Antistatic plastic tube					

LINKS TO RELATED DOCUMENTS					
Dimensions	D ² PAK (TO-263AB)	www.vishay.com/doc?96164			
Differsions	TO-262AA	www.vishay.com/doc?96165			
Dout moulcing information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444			
Part marking information	TO-262AA	www.vishay.com/doc?95443			
Packaging information		www.vishay.com/doc?96424			
SPICE model		www.vishay.com/doc?95357			

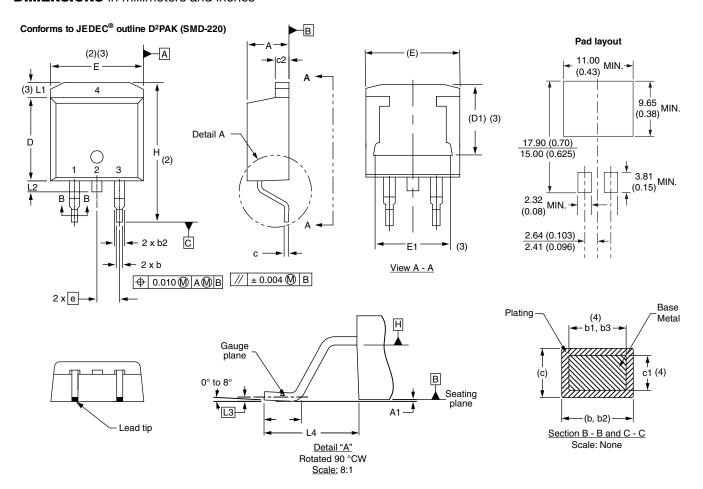
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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	IETERS	INCHES		NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIMETERS INCHES		NOTES		
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
Е	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	2.54 BSC		0.100 BSC	
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 1 Document Number: 96164

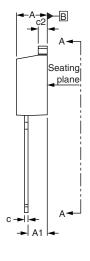


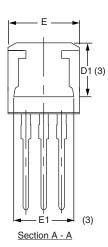
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TO-262AA

DIMENSIONS in millimeters and inches

Modified JEDEC® outline TO-262 (2) (3) (3) Ď L2 (2)





♦0.010**M**A**M**B

2 x e

Lead assignments



Diodes 1. - Anode (two die)/open (one die)

2., 4. - Cathode

3. - Anode

-3 x b2

-3 x b

Plating –	(4) b1, b3	Base / metal
C C		c1 (4)
	← (b, b2) →	_

Section B - B and C - C Scale: None

SYMBOL	MILLIN	MILLIMETERS		INCHES		
STWIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54	2.54 BSC		0 BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
 (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- Controlling dimension: inches

 Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

Revision: 30-Nov-17 Document Number: 96165

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